

R-C Thermal Model Parameters

DESCRIPTION

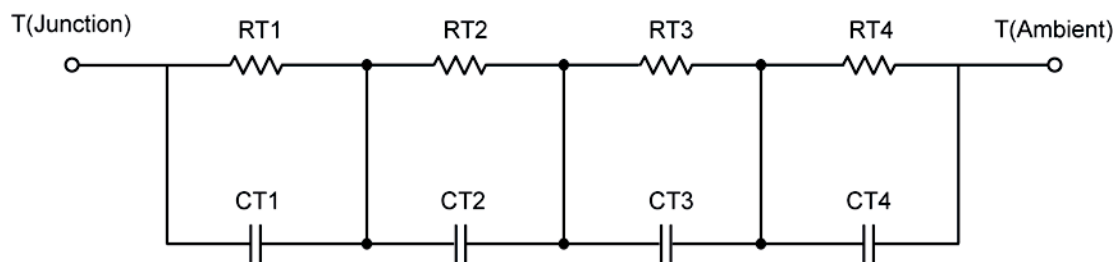
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

For a detailed explanation of implementing these values in P-SPIICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPIICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	14.8529	N/A	3.4494
RT2	41.2600	N/A	28.8139
RT3	37.6450	N/A	17.1891
RT4	56.2420	N/A	15.5475
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	4.2330 m	N/A	1.2679 m
CT2	35.5212 m	N/A	39.6349 m
CT3	12.6468 m	N/A	11.9746 m
CT4	1.3775	N/A	11.3457 m

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ($^{\circ}\text{C}/\text{W}$)			
Junction to	Ambient	Case	Foot
RF1	21.5898	N/A	15.2167
RF2	35.7462	N/A	22.5989
RF3	36.9213	N/A	13.2464
RF4	55.7426	N/A	13.9380
Thermal Capacitance (Joules/ $^{\circ}\text{C}$)			
Junction to	Ambient	Case	Foot
CF1	2.6552 m	N/A	2.2692 m
CF2	4.6291 m	N/A	4.8960 m
CF3	17.5964 m	N/A	3.8677 m
CF4	1.3224	N/A	74.9097 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

